



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

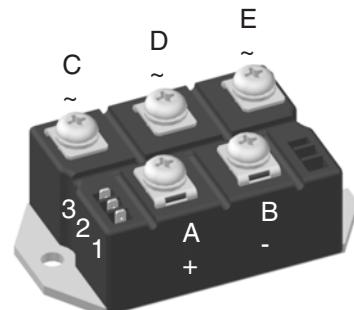
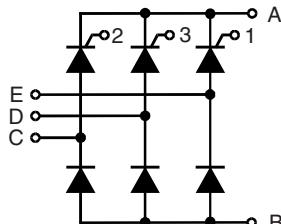
Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

Three Phase Half Controlled Rectifier Bridge, B6HK

$I_{dAVM} = 110/167 A$
 $V_{RRM} = 1200-1600 V$

V_{RSM} V_{DSM}	V_{RRM} V_{DRM}	Type
V	V	
1300 1700	1200 1600	VVZ 110-12io7 VVZ 175-16io7



Symbol	Test Conditions	Maximum Ratings		
		VVZ 110	VVZ 175	
I_{dAV}	$T_c = 85^\circ C$; module per leg	110	167	A
I_{FRMS}, I_{TRMS}		58	89	A
I_{FSM}, I_{TSM}	$T_{VJ} = 45^\circ C$; $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1150	1500	A
	$T_{VJ} = T_{VJM}$ $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1230	1600	A
I^2t	$T_{VJ} = 45^\circ C$ $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1000	1350	A
	$T_{VJ} = T_{VJM}$ $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1070	1450	A
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ repetitive, $I_T = 50 \text{ A}$ $f = 400 \text{ Hz}$, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$, non repetitive, $di_G/dt = 0.3 \text{ A}/\mu\text{s}$, $I_T = 1/3 \cdot I_{dAV}$	6600	11200	$A^2\text{s}$
		6280	10750	$A^2\text{s}$
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	5000	9100	$A^2\text{s}$
		4750	8830	$A^2\text{s}$
V_{RGM}		150	500	$A/\mu\text{s}$
P_{GM}	$T_{VJ} = T_{VJM}$ $t_p = 30 \mu\text{s}$ $I_T = I_{TAVM}$ $t_p = 500 \mu\text{s}$ $t_p = 10 \text{ ms}$	\leq \leq \leq	10 5 1	W
			0.5	W
P_{GAVM}		-40...+125	125	$^\circ\text{C}$
T_{VJ}		125	125	$^\circ\text{C}$
T_{VJM}		-40...+125	-40...+125	$^\circ\text{C}$
T_{stg}				
V_{ISOL}	50/60 Hz, RMS $t = 1 \text{ min}$	2500	2500	$V\sim$
	$I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	3000	3000	$V\sim$
M_d	Mounting torque (M6) Terminal connection torque (M6)	5±15 %	5±15 %	Nm
Weight	typ.	300	300	g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

IXYS reserves the right to change limits, test conditions and dimensions.

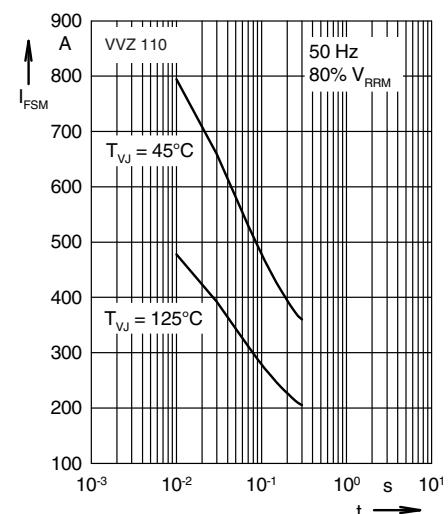
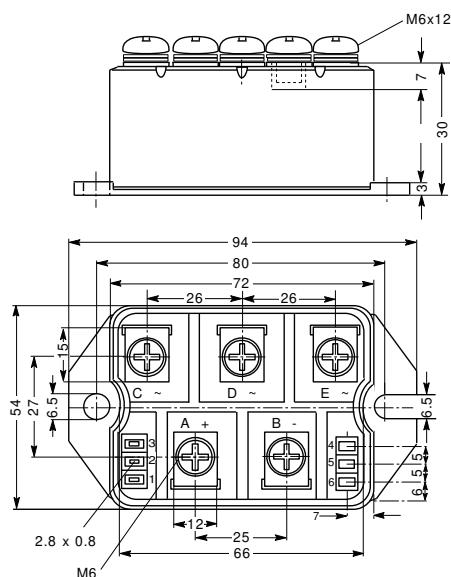
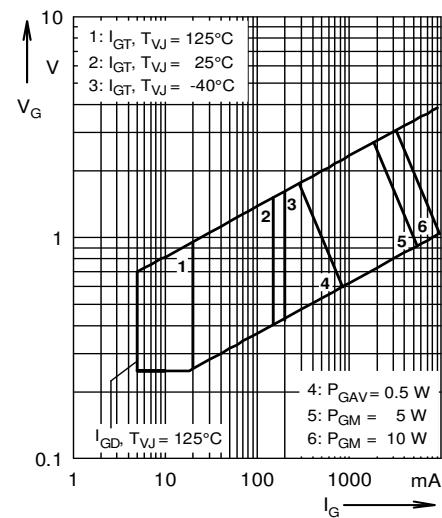
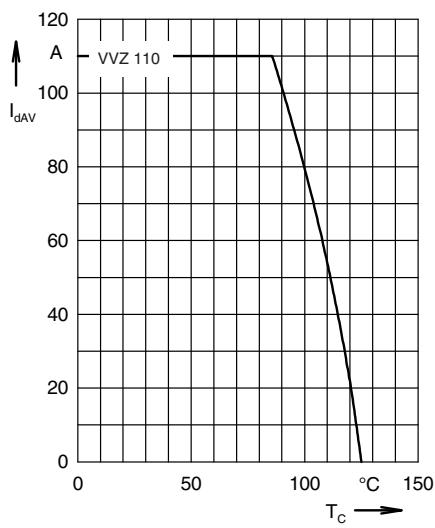
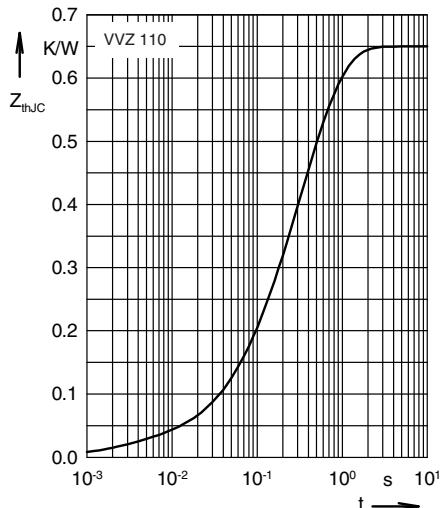
© 2010 IXYS All rights reserved

20100706b

1 - 2

Symbol
Test Conditions
Characteristic Values
VVZ 110 | VVZ 175

I_R, I_D	$V_R = V_{RRM}; V_D = V_{DRM}$	$T_{VJ} = T_{VJM}$ $T_{VJ} = 25^\circ C$	\leq	5	mA
			\leq	0.3	mA
V_F, V_T	$I_F, I_T = 200 A, T_{VJ} = 25^\circ C$		\leq	1.75	V
V_{TO} r_T	For power-loss calculations only $(T_{VJ} = 125^\circ C)$		0.85	0.85	V
			6	3.5	$m\Omega$
V_{GT}	$V_D = 6 V;$ $T_{VJ} = 25^\circ C$	\leq	1.5		V
	$T_{VJ} = -40^\circ C$	\leq	1.6		V
I_{GT}	$V_D = 6 V;$ $T_{VJ} = 25^\circ C$	\leq	100		mA
	$T_{VJ} = -40^\circ C$	\leq	200		mA
V_{GD} I_{GD}	$T_{VJ} = T_{VJM};$ $T_{VJ} = T_{VJM};$	$V_D = \frac{2}{3} V_{DRM}$ $V_D = \frac{2}{3} V_{DRM}$	\leq	0.2	V
			\leq	5	mA
I_L	$I_G = 0.3 A; t_g = 30 \mu s$ $di_G/dt = 0.3 A/\mu s$	$T_{VJ} = 25^\circ C$	\leq	450	mA
I_H	$T_{VJ} = 25^\circ C; V_D = 6 V; R_{GK} = \infty$		\leq	200	mA
t_{gd}	$T_{VJ} = 25^\circ C; V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$		\leq	2	μs
R_{thJC}	per thyristor (diode); DC current		0.65	0.46	K/W
	per module		0.108	0.077	K/W
R_{thJH}	per thyristor (diode); DC current		0.8	0.55	K/W
	per module		0.133	0.092	K/W
d_s	Creeping distance on surface		10		mm
d_A	Creepage distance in air		9.4		mm
a	Max. allowable acceleration		50		m/s^2

Dimensions in mm (1 mm = 0.0394")

Fig. 3 Surge overload current
 I_{FSM} : Crest value, t : duration

Fig. 1 Gate trigger characteristics

Fig. 2 DC output current at case temperature

Fig. 4 Transient thermal impedance junction to case (per leg)